

2N6344

Preferred Device

Triacs Silicon Bidirectional Thyristors

Designed primarily for full-wave ac control applications, such as light dimmers, motor controls, heating controls and power supplies; or wherever full-wave silicon gate controlled solid-state devices are needed. Triac type thyristors switch from a blocking to a conducting state for either polarity of applied main terminal voltage with positive or negative gate triggering.

Features

- Blocking Voltage to 800 V
- All Diffused and Glass Passivated Junctions for Greater Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Gate Triggering Guaranteed in all Four Quadrants
- For 400 Hz Operation, Consult Factory
- Pb-Free Package is Available*

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

| Rating | Symbol | Value | Unit |
|---|--|-------------|------------------|
| †Peak Repetitive Off-State Voltage (Note 1) (T _J = -40 to +110°C, Sine Wave 50 to 60 Hz, Gate Open) | V _{DRM} , V _{RRM} | 600 800 | V |
| †On-State RMS Current (T _C = +80°C) Full Cycle Sine Wave 50 to 60 Hz (T _C = +90°C) | I _{T(RMS)} | 8.0 4.0 | A |
| †Peak Non-Repetitive Surge Current (One Full Cycle, Sine Wave 60 Hz, T _C = +25°C) Preceded and followed by rated current | I _{TSM} | 100 | A |
| Circuit Fusing Consideration (t = 8.3 ms) | I ² t | 40 | A ² s |
| †Peak Gate Power (T _C = +80°C, Pulse Width = 2 μs) | P _{GM} | 20 | W |
| †Average Gate Power (T _C = +80°C, t = 8.3 ms) | P _{G(AV)} | 0.5 | W |
| †Peak Gate Current (T _C = +80°C, Pulse Width = 2.0 μs) | I _{GM} | 2.0 | A |
| †Peak Gate Voltage (T _C = +80°C, Pulse Width = 2.0 μs) | V _{GM} | 10 | V |
| †Operating Junction Temperature Range | T _J | -40 to +125 | °C |
| Storage Temperature Range | T _{stg} | -40 to +150 | °C |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

†Indicates JEDEC Registered Data.

1. V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

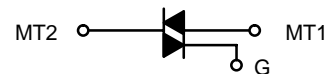
*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



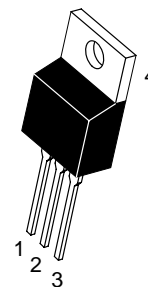
ON Semiconductor®

<http://onsemi.com>

**TRIACS
8 AMPERES RMS
600 thru 800 VOLTS**



MARKING DIAGRAM



**TO-220AB
CASE 221A
STYLE 4**



A = Assembly Location
Y = Year
WW = Work Week
G = Pb-Free Package

PIN ASSIGNMENT

| | |
|---|-----------------|
| 1 | Main Terminal 1 |
| 2 | Main Terminal 2 |
| 3 | Gate |
| 4 | Main Terminal 2 |

ORDERING INFORMATION

| Device | Package | Shipping |
|---------|-----------------------|-----------------|
| 2N6344 | TO-220AB | 500 Units / Box |
| 2N6344G | TO-220AB (Pb-Free) | 500 Units / Box |

Preferred devices are recommended choices for future use and best overall value.

2N6344

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|---|-----------------|-----|------|
| †Thermal Resistance, Junction-to-Case | $R_{\theta JC}$ | 2.2 | °C/W |
| Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Sec | T_L | 260 | °C |

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted; Electricals apply in both directions)

| Characteristic | Symbol | Min | Typ | Max | Unit |
|----------------|--------|-----|-----|-----|------|
|----------------|--------|-----|-----|-----|------|

OFF CHARACTERISTICS

| | | | | | |
|--|--------------------|---|---|-----|---------------------------|
| †Peak Repetitive Blocking Current ($V_D = \text{Rated } V_{DRM}, V_{RRM}; \text{ Gate Open}$) | I_{DRM}, I_{RRM} | - | - | 10 | μA |
| | | - | - | 2.0 | mA |
| | | | | | $T_J = 25^\circ\text{C}$ |
| | | | | | $T_J = 100^\circ\text{C}$ |

ON CHARACTERISTICS

| | | | | | |
|--|-------------|-----|-----|------|----------------------------|
| †Peak On-State Voltage ($I_{TM} = \pm 11 \text{ A Peak}; \text{ Pulse Width} = 1 \text{ to } 2 \text{ ms}, \text{ Duty Cycle} \leq 2\%$) | V_{TM} | - | 1.3 | 1.55 | V |
| Gate Trigger Current (Continuous dc) ($V_D = 12 \text{ Vdc}, R_L = 100 \Omega$) | I_{GT} | | | | mA |
| Quadrant I: MT2(+), G(+) | Both | - | 12 | 50 | |
| Quadrant II: MT2(+), G(-) | 2N6349 only | - | 12 | 75 | |
| Quadrant III: MT2(-), G(-) | Both | - | 20 | 50 | |
| Quadrant IV: MT2(-), G(+) | 2N6349 only | - | 35 | 75 | |
| †MT2(+), G(+); MT2(-), G(-) $T_C = -40^\circ\text{C}$ | | - | - | 100 | |
| †MT2(+), G(-); MT2(-), G(+), $T_C = -40^\circ\text{C}$ | | - | - | 125 | |
| Gate Trigger Voltage (Continuous dc) ($V_D = 12 \text{ Vdc}, R_L = 100 \Omega$) | V_{GT} | | | | V |
| Quadrant I: MT2(+), G(+) | Both | - | 0.9 | 2.0 | |
| Quadrant II: MT2(+), G(-) | 2N6349 only | - | 0.9 | 2.5 | |
| Quadrant III: MT2(-), G(-) | Both | - | 1.1 | 2.0 | |
| Quadrant IV: MT2(-), G(+) | 2N6349 only | - | 1.4 | 2.5 | |
| †MT2(+), G(+); MT2(-), G(-) $T_C = -40^\circ\text{C}$ | | - | - | 2.5 | |
| †MT2(+), G(-); MT2(-), G(+), $T_C = -40^\circ\text{C}$ | | - | - | 3.0 | |
| Gate Non-Trigger Voltage (Continuous dc) ($V_D = \text{Rated } V_{DRM}, R_L = 10 \text{ k}\Omega, T_J = 100^\circ\text{C}$) | V_{GD} | | | | V |
| †MT2(+), G(+); MT2(-), G(-); MT2(+), G(-); MT2(-), G(-) | | 0.2 | - | - | |
| †Holding Current ($V_D = 12 \text{ Vdc}, \text{ Gate Open}$) (Initiating Current = $\pm 200 \text{ mA}$) | I_H | | | | mA |
| | | - | 6.0 | 40 | |
| | | - | - | 75 | |
| | | | | | $T_C = 25^\circ\text{C}$ |
| | | | | | $*T_C = -40^\circ\text{C}$ |
| †Turn-On Time ($V_D = \text{Rated } V_{DRM}, I_{TM} = 11 \text{ A}, I_{GT} = 120 \text{ mA}, \text{ Rise Time} = 0.1 \mu\text{s}, \text{ Pulse Width} = 2 \mu\text{s}$) | t_{gt} | - | 1.5 | 2.0 | μs |

DYNAMIC CHARACTERISTICS

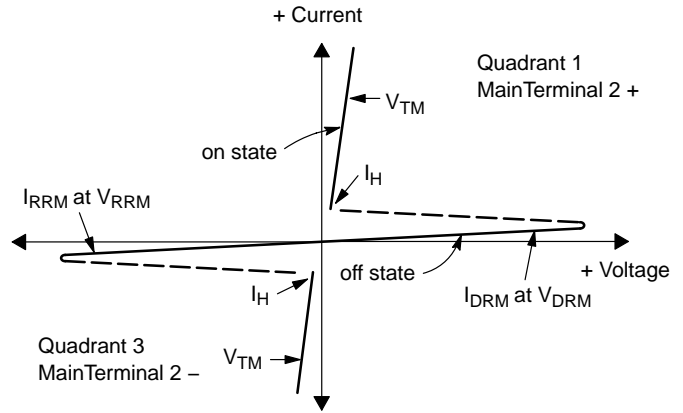
| | | | | | |
|---|------------|---|-----|---|------------------|
| Critical Rate of Rise of Commutation Voltage ($V_D = \text{Rated } V_{DRM}, I_{TM} = 11 \text{ A}, \text{ Commutating } di/dt = 4.0 \text{ A/ms}, \text{ Gate Unenergized}, T_C = 80^\circ\text{C}$) | $dv/dt(c)$ | - | 5.0 | - | V/ μs |
|---|------------|---|-----|---|------------------|

†Indicates JEDEC Registered Data.

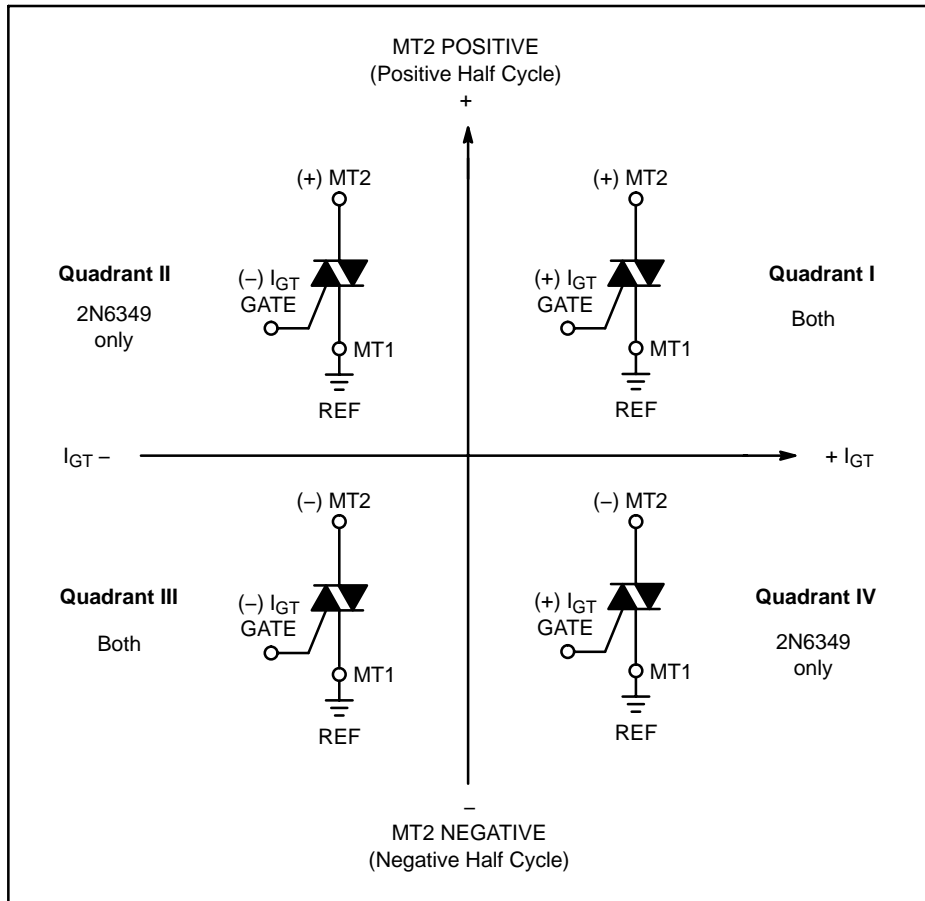
2N6344

Voltage Current Characteristic of Triacs (Bidirectional Device)

| Symbol | Parameter |
|-----------|---|
| V_{DRM} | Peak Repetitive Forward Off State Voltage |
| I_{DRM} | Peak Forward Blocking Current |
| V_{RRM} | Peak Repetitive Reverse Off State Voltage |
| I_{RRM} | Peak Reverse Blocking Current |
| V_{TM} | Maximum On State Voltage |
| I_H | Holding Current |



Quadrant Definitions for a Triac



All polarities are referenced to MT1.
 With in-phase signals (using standard AC lines) quadrants I and III are used.

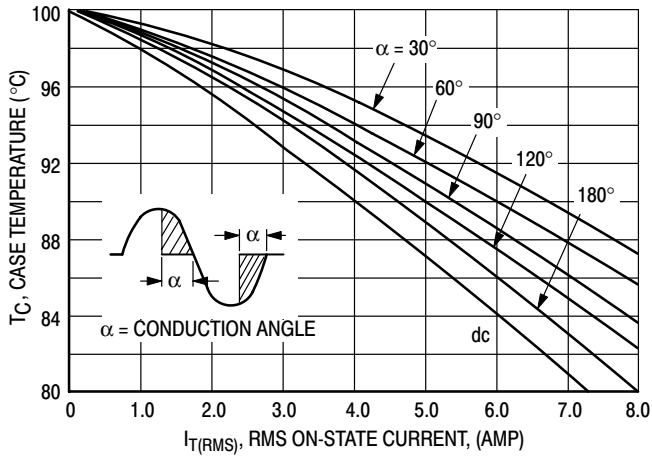


Figure 1. RMS Current Derating

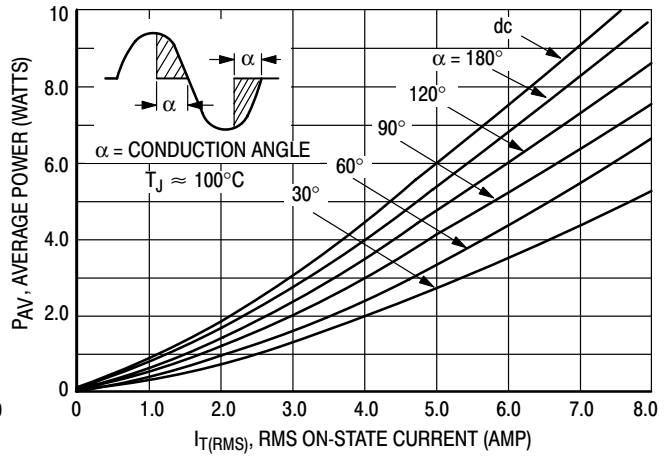


Figure 2. On-State Power Dissipation

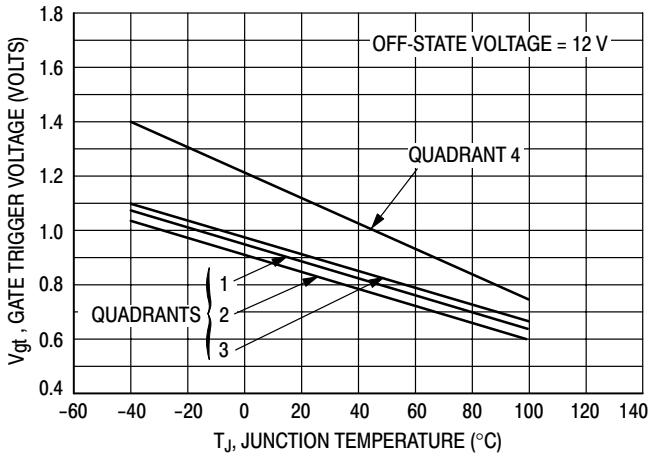


Figure 3. Typical Gate Trigger Voltage

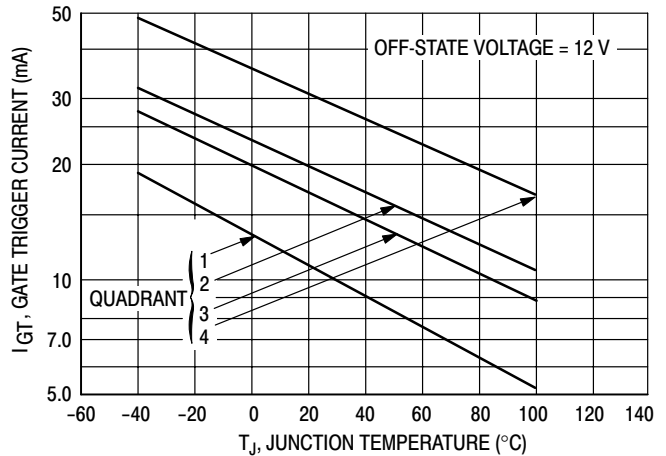


Figure 4. Typical Gate Trigger Current

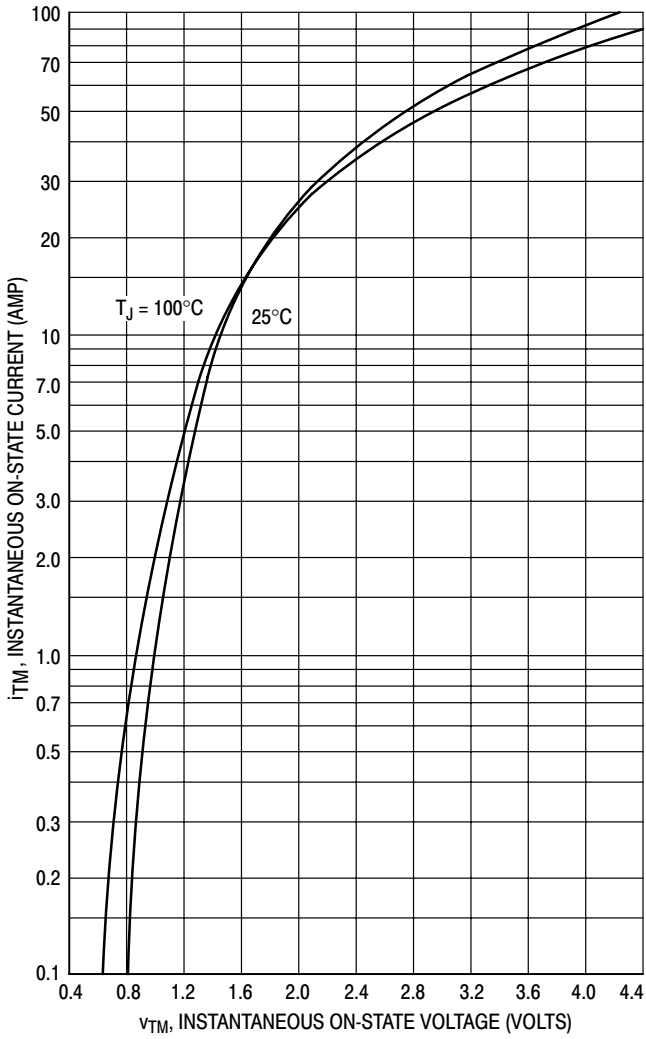


Figure 5. On-State Characteristics

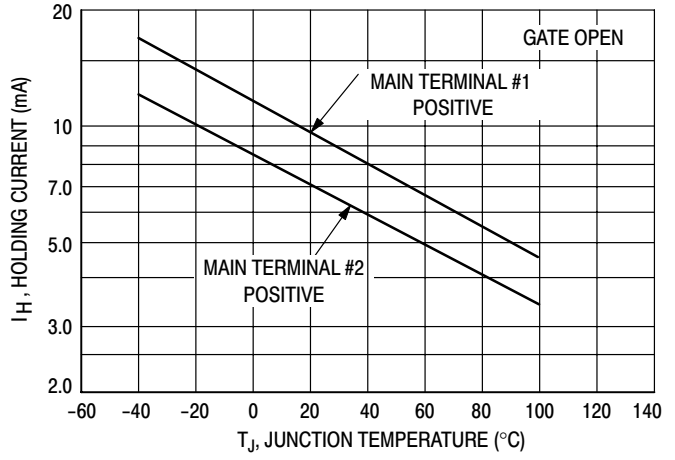


Figure 6. Typical Holding Current

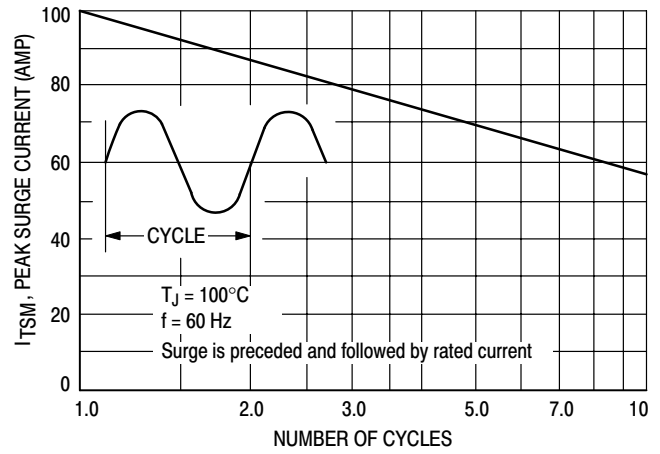


Figure 7. Maximum Non-Repetitive Surge Current

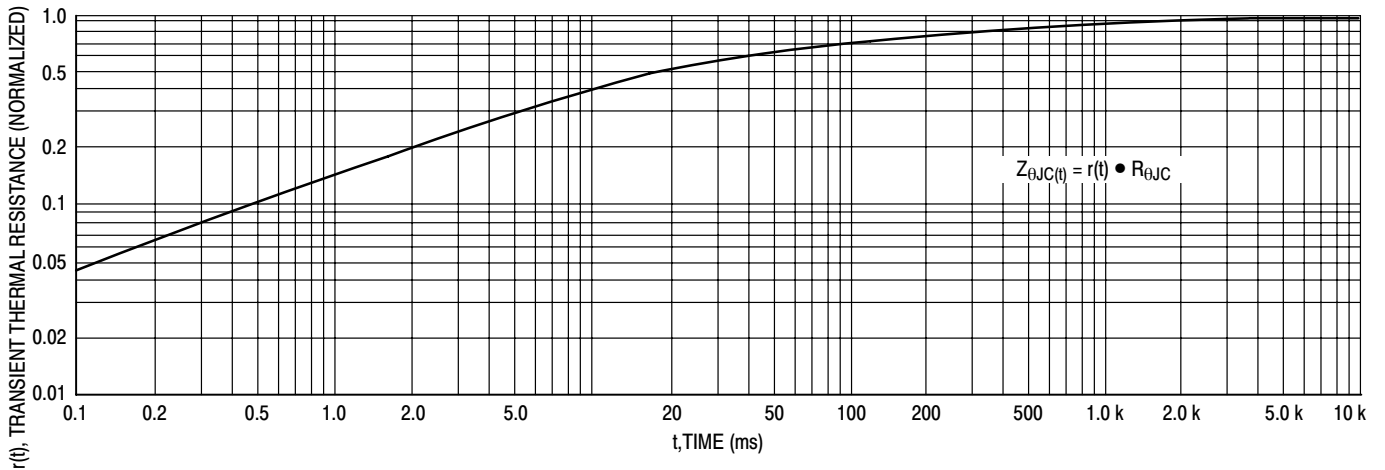
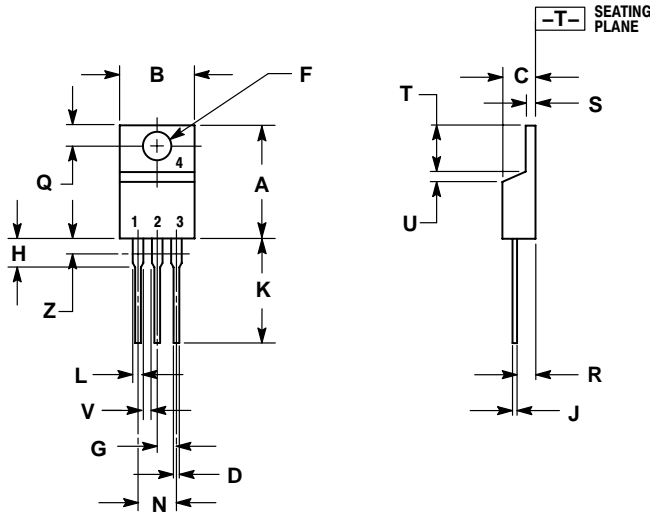


Figure 8. Typical Thermal Response

2N6344

PACKAGE DIMENSIONS

TO-220AB
CASE 221A-07
ISSUE AA



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

| DIM | INCHES | | MILLIMETERS | |
|-----|--------|-------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | 0.570 | 0.620 | 14.48 | 15.75 |
| B | 0.380 | 0.405 | 9.66 | 10.28 |
| C | 0.160 | 0.190 | 4.07 | 4.82 |
| D | 0.025 | 0.035 | 0.64 | 0.88 |
| F | 0.142 | 0.147 | 3.61 | 3.73 |
| G | 0.095 | 0.105 | 2.42 | 2.66 |
| H | 0.110 | 0.155 | 2.80 | 3.93 |
| J | 0.014 | 0.022 | 0.36 | 0.55 |
| K | 0.500 | 0.562 | 12.70 | 14.27 |
| L | 0.045 | 0.060 | 1.15 | 1.52 |
| N | 0.190 | 0.210 | 4.83 | 5.33 |
| Q | 0.100 | 0.120 | 2.54 | 3.04 |
| R | 0.080 | 0.110 | 2.04 | 2.79 |
| S | 0.045 | 0.055 | 1.15 | 1.39 |
| T | 0.235 | 0.255 | 5.97 | 6.47 |
| U | 0.000 | 0.050 | 0.00 | 1.27 |
| V | 0.045 | --- | 1.15 | --- |
| Z | --- | 0.080 | --- | 2.04 |

- STYLE 4:
1. MAIN TERMINAL 1
 2. MAIN TERMINAL 2
 3. GATE
 4. MAIN TERMINAL 2

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